Film in tension

$G = Z \sigma^2 h/\overline{E}_f$ Cracking Patterns Surface Crack 7 = 3.951Channeling Z = 1.976Substrate Damage Z = 3.951Spalling Z = 0.343

Fig. 43. Commonly observed cracking patterns. The dimensionless driving force for each pattern is listed, assuming that the film-substrate is elastically homogeneous, and the substrate is infinitely thick.

Film in compression

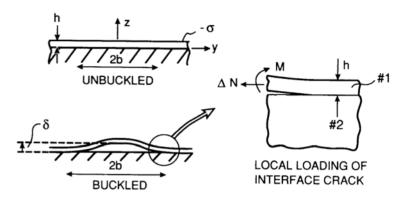
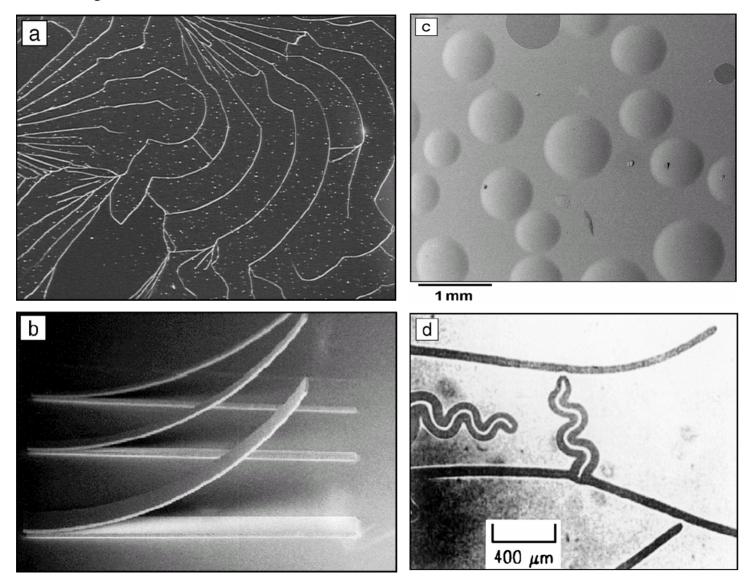


Fig. 57. Geometry of the one-dimensional blister, and conventions for the elasticity solution characterizing conditions near the tip of an interface crack between a thin film and an infinitely thick substrate. Top left: unbuckled; bottom left: buckled; right: local loading of interface crack.

Hutchinson, Suo Advances in Applied Mechanics 29, 64-192 (1992).

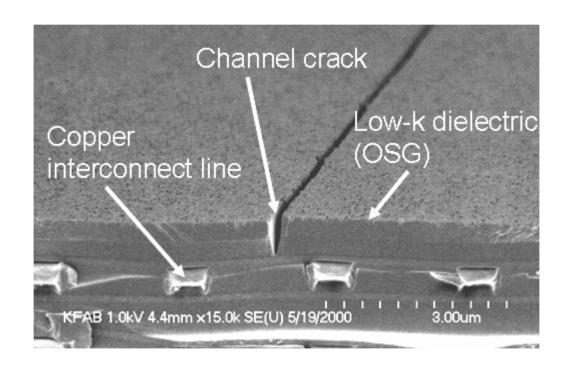
pdf file: www.deas.harvard.edu/suo

Variety of Thin Film Fracture Patterns



2

A channel crack



T. Tsui (http://www.imechanica.org/node/248)

The origin of stress in a film

- Deposition process (intrinsic stress)
- Mismatch due to lattice constant
- Mismatch in the coefficient of thermal expansion
- Bending

W.D. Nix, Mechanical Properties of Thin Films (http://imechanica.org/node/530)

Stress in a thin film due to mismatch in the coefficients of thermal expansion

- •The film is very thin compared to the substrate (h << H).
- •The substrate is nearly stress free.
- •The film is in a state of equal biaxial stress, σ .
- •At T_{ref}, the film is stress free.
- •The film deforms elastically as the temperature changes

$$\varepsilon_{s} = \alpha_{s} \left(T - T_{ref} \right) \qquad \qquad \varepsilon_{f} = \alpha_{f} \left(T - T_{ref} \right) + \frac{\left(1 - \nu_{f} \right) \sigma}{E_{f}}$$

As the temperature changes, the substrate and the film remains bonded

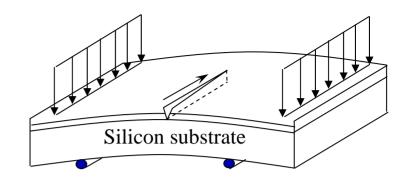
$$\varepsilon_{s} = \varepsilon_{f}$$

$$\sigma = \frac{E_{f}}{(1 - \nu_{f})} (\alpha_{f} - \alpha_{s}) (T_{ref} - T)$$

When $\alpha_f > \alpha_s$, upon cooling, the film is under tensile stress, $\sigma > 0$. 5

Stress in film due to bending

$$\frac{1}{R} = \frac{M}{\frac{E_s}{12\left(1 - v_s^2\right)}BH^3}$$



$$\varepsilon = \frac{H/2}{R}$$

$$\sigma = \frac{E_f}{1 - v_f^2} \varepsilon$$

$$\sigma = \frac{6E_f \left(1 - v_s^2\right)M}{E_s \left(1 - v_f^2\right)BH^2}$$

M = applied moment

B = width of the beam

H = thickness of the substrate

R = radius of curvature

 $\varepsilon = \text{strain in the film}$

 σ = stress in the film

Measure residual stress using wafer curvature

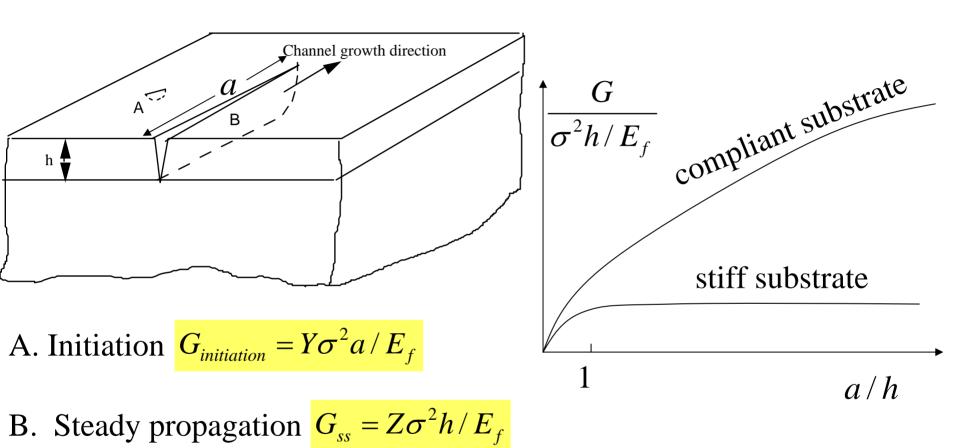
$$f = \int \sigma dz$$

$$M = fBH/2$$

$$\frac{1}{R} = \frac{1 - v_s}{E_s} \frac{12M}{BH^3}$$

$$f = \left(\frac{E_s}{1 - \nu_s}\right) \frac{H^2}{6R}$$

Channel crack: Initiation vs. steady propagation



When the substrate is compliant, steady state is attained at a large a/h and a large energy release rate.

Steady-state energy release rate of a channel crack

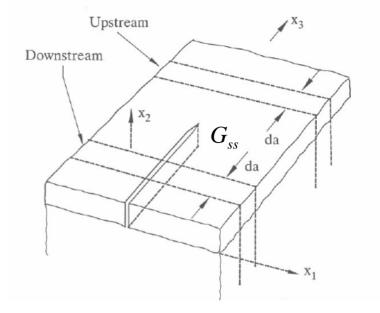
Reduction in elastic energy for the crack to advance a unit distance

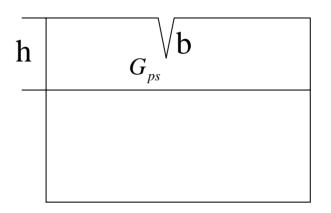
$$U = SE_{upstream} - SE_{downstream}$$

$$U = \int_{0}^{h} G_{ps}(b)$$

Steady-state energy release rate

$$hG_{ss} = U$$
 $G_{ss} = \frac{1}{h} \int_{0}^{h} G_{ps}(b) db$





Example: film and substrate have similar elastic modulus

$$G_{ps}(b) = \frac{1-v^2}{E} (1.1215)^2 \pi b \sigma^2$$

$$G_{ss} = 2\frac{\left(1 - v^2\right)}{E}h\sigma^2$$

Steady-state energy release rate of a channel crack

Reduction in elastic energy for the crack

to advance a unit distance

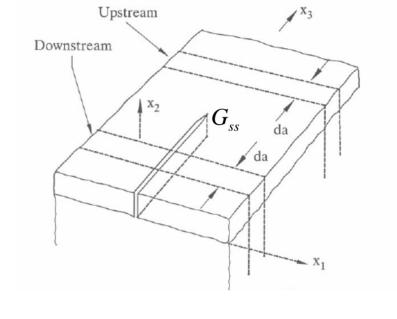
$$U = SE_{upstream} - SE_{downstream}$$

$$U = \frac{1}{2} \int_{0}^{h} \delta(z) \sigma(z) dz$$

 $\delta(z)$ Crack opening downstream

$$\sigma(z)$$
 Stress upstream

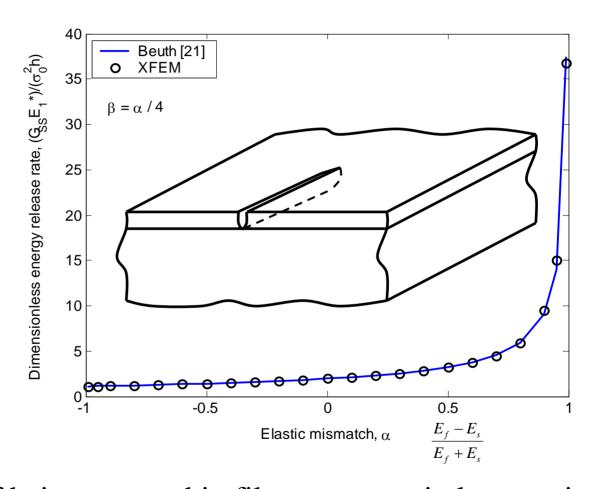
$$hG_{ss} = U$$



$$G_{ss} = \frac{1}{2h} \int_{0}^{h} \delta(z) \sigma(z) dz$$

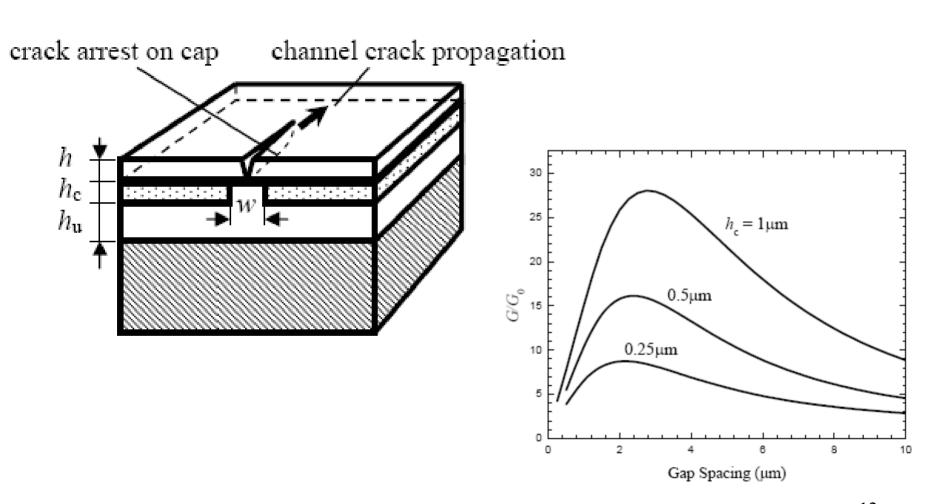
Driving force for steady propagation

$$G_{ss} = Z \frac{\sigma^2 h}{E_f}$$



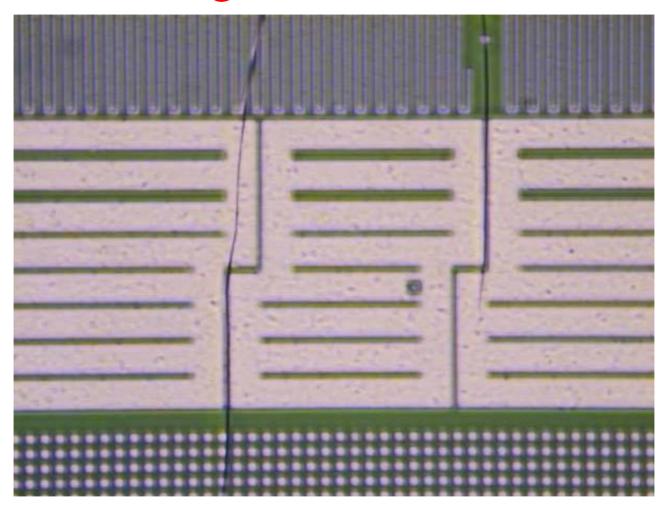
An advantage of being nano: thin films can sustain large stains. e.g., 7 nm silica film can sustain strains of ~5%.

Channel crack in patterned structure



12

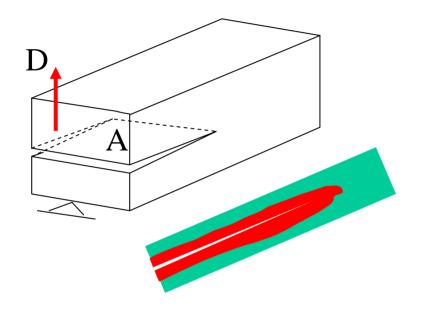
Cracking in low k dielectrics



Also see a thread of discussion at http://www.imechanica.org/node/165

Crack driving force, G

Generalized coordinates: D = displacement, A = crack area



Elastic energy
$$U(D, A)$$

$$dU = FdD - GdA$$

$$G = -\frac{\partial U(D, A)}{\partial A}$$

Work supply = elastic energy + excess

In *steady state*, the excess is proportional to crack area, ΓA

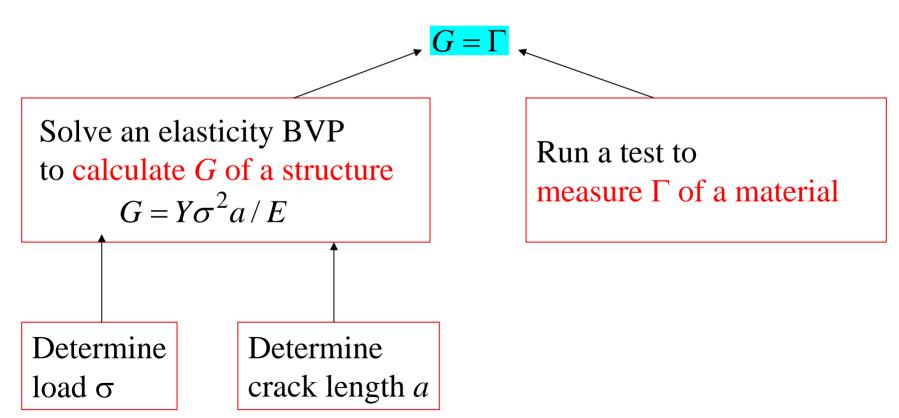
$$FdD = dU + \Gamma dA$$

$$G = \Gamma$$

Fracture mechanics as a division of labor

George Rankin Irwin (1907-1998)

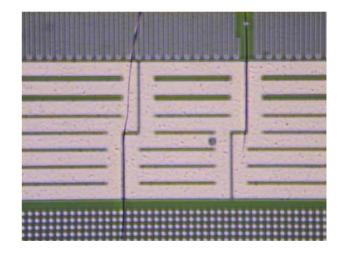
Crack driving force, G. Crack resistance, Γ



Small structures: a new economy

Calculating G is prohibitively expensive

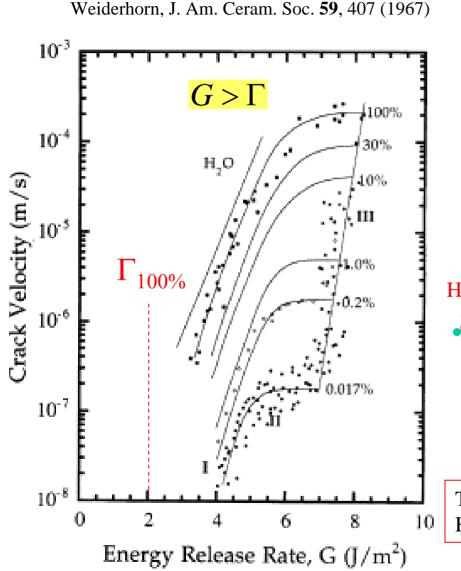
- •3D architecture
- •uncertain flaws
- •uncertain residual stress field
- •uncertain material properties

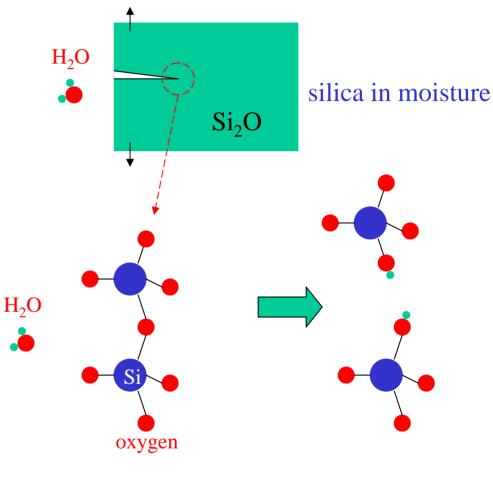


• Massive testing is cheap.

A new division of labor: run test to measure G!

Moisture-assisted crack growth: the V-G function





The load opens crack and strains bonds
H₂O transports to crack tip and assists in breaking bonds

A method to measure G

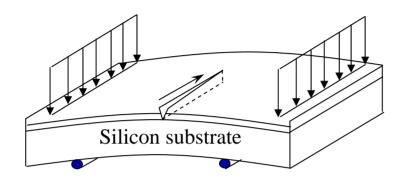
V-G function is specific to material and environment, and remains the same when the material is integrated into a structure.

Use a simple structure to measure V-G function.

In a complex structure, an observed V gives a reading of G.

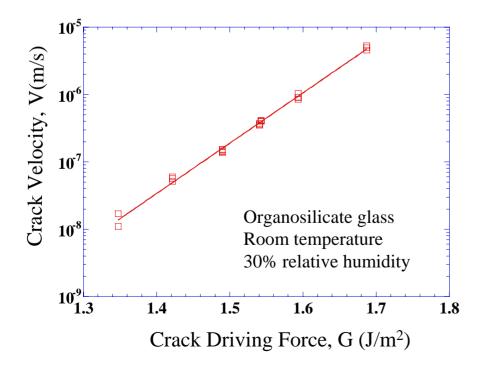
...in a way analogous to measuring temperature

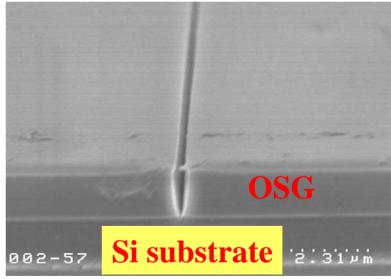
Measure the V-G function



- Scratch and bend
- •Channel crack

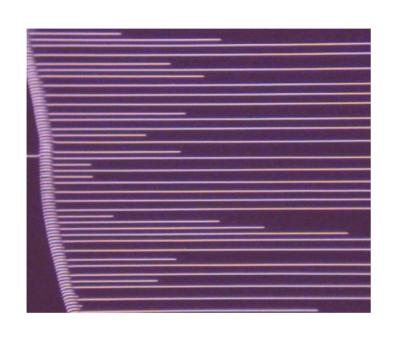
$$G = Z\sigma^2 h / \overline{E}$$

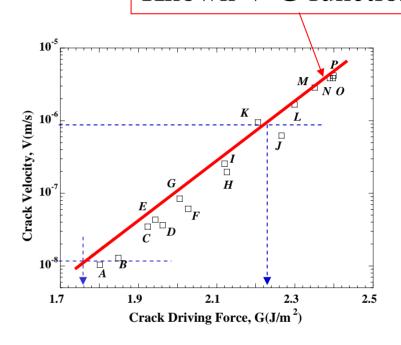




Read G

Known V-G function





$$G = \frac{\sigma^2 Zh}{\overline{E}} \left(\tanh \left(\frac{S_1}{2Zh} \right) + \tanh \left(\frac{S_2}{2Zh} \right) - \tanh \left(\frac{S_1 + S_2}{2Zh} \right) \right)$$

Measure crack driving force due to residual stress field, G_R

At G_R, the crack velocity is too low to be observed.

- •Bend structure, observe crack velocity, and read G.
- •Extrapolate the data to obtain G_R

